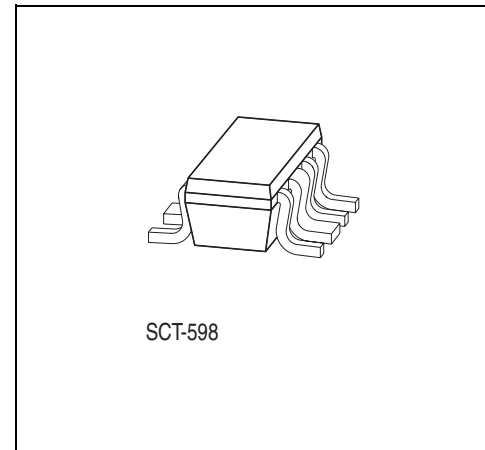


## GaAs MMIC

### Preliminary Data Sheet

**CSY 210**

- TX/RX- and diversity switch for mobile communications
- High input power capability (36 dBm  $P_{-1\text{ dB}}$  @ 3 V operation, 900 MHz)
- High linearity (57 dBm IP3 @ 900 MHz)
- Low insertion loss (0.6 dB @ 900 MHz)
- Positive control- and supply voltages (3 V)
- Miniature package SCT-598



**ESD: Electrostatic discharge sensitive device, observe handling precautions!**

Type	Marking	Ordering Code (taped)	Package <sup>1)</sup>
CSY 210	on request	on request	SCT-598

<sup>1)</sup> Dimensions see **Page 9**.

### Maximum Ratings

Parameter	Symbol	Value	Unit
Control voltage range	$V_A/V_B$	t.b.d.	V
Channel temperature	$T_{Ch}$	150	°C
Storage temperature range	$T_{stg}$	- 55 ... + 150	°C
Total power dissipation ( $T_S \leq \text{t.b.d. } ^\circ\text{C}$ ) <sup>1)</sup>	$P_{tot}$	t.b.d.	mW
Input Power	$P_{IN}$	t.b.d.	mW

<sup>1)</sup> Please care for sufficient heat dissipation on the pcb!

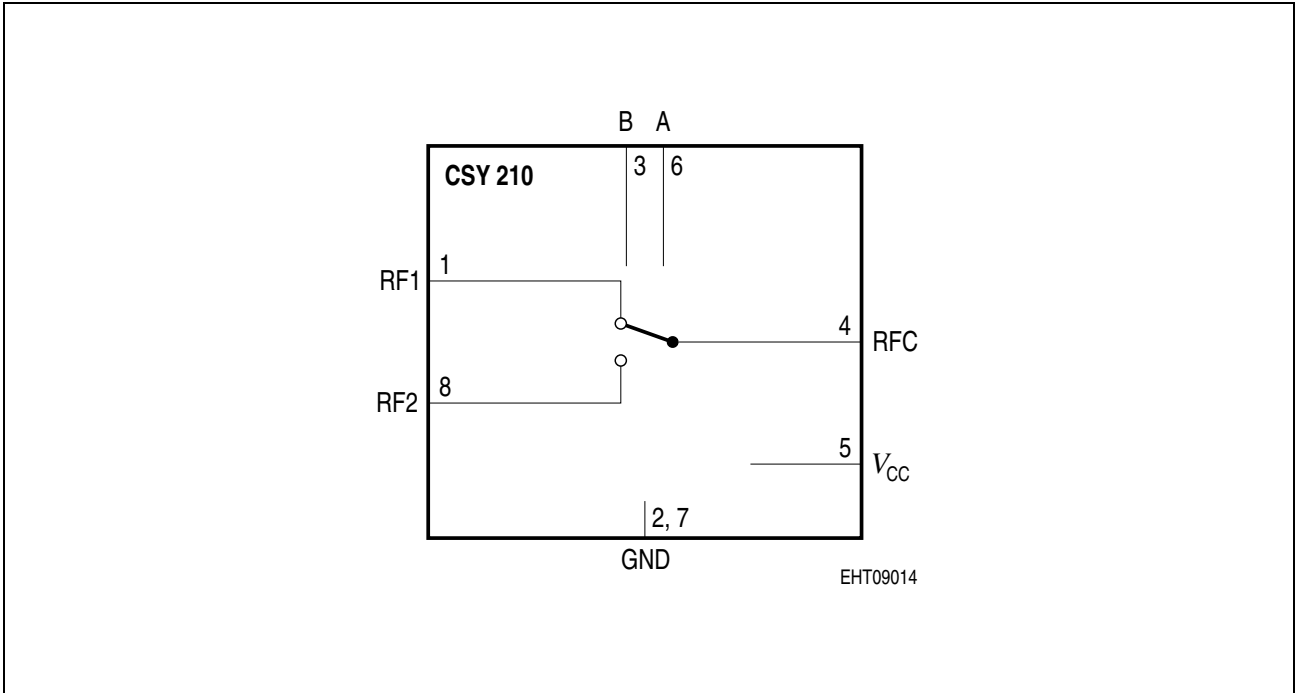


Figure 1 Functional Block Diagram

**Electrical Characteristics**
 $(T_A = 25\text{ }^\circ\text{C}; P_{IN} = 10\text{ dBm, unless otherwise stated})$ 

Parameter	Symbol	Limit Values			Unit	Test Conditions
		min.	typ.	max.		
Insertion Loss RF1 - RFC $f = 0.9\text{ GHz}$ $f = 1.8\text{ GHz}$	$IL_{RF1}$	–	0.6 0.9	–	dB	$V_A = 0\text{ V,}$ $V_B = 3\text{ V,}$ $V_{CC} = 3\text{ V}$
Insertion Loss RF2 - RFC $f = 0.9\text{ GHz}$ $f = 1.8\text{ GHz}$	$IL_{RF2}$	–	0.6 0.9	–	dB	$V_A = 3\text{ V,}$ $V_B = 0\text{ V,}$ $V_{CC} = 3\text{ V}$
Isolation RF1 - RF2 $f = 0.9\text{ GHz}$ $f = 1.8\text{ GHz}$	ISO	–	17 12	–	dB	$V_A = 0\text{ V,}$ $V_B = 3\text{ V,}$ $V_{CC} = 3\text{ V}$
Input power at 1 dB gain compression (RF1 - RFC) Pulsed: $T_{ON} = 577\text{ }\mu\text{s,}$ 12.5% duty cycle	$P_{-1\text{ dB}}$	–	36	–	dBm	$V_A = 0\text{ V,}$ $V_B = 3\text{ V,}$ $V_{CC} = 3\text{ V}$ $f = 0.9\text{ GHz}$
Input power at 1 dB gain compression (RF1 - RFC) 100% duty cycle	–	–	34.5	–	dBm	–
Third order intercept point Two tone input power = 18 dBm each $f = 0.8\text{ GHz}$ $f = 1.9\text{ GHz}$	IP3	–	57 57	–	dBm	$V_{CC} = 3\text{ V,}$ $V_{A,B} = 0\text{ V (3 V)}$
VSWR (RF1 - RFC; RF2 - RFC) 0.5 GHz - 2 GHz	VSWR	–	1.2:1	–	–	–
Control current	–	–	–	100	$\mu\text{A}$	–
Supply current	–	–	–	100	$\mu\text{A}$	–

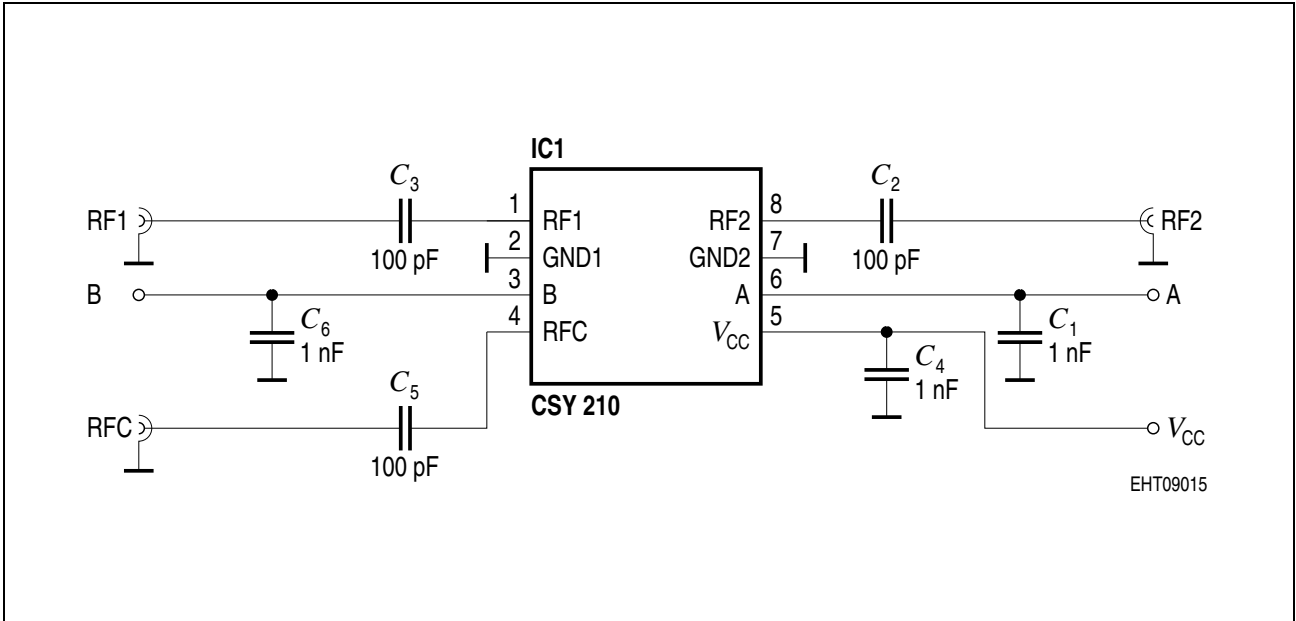


Figure 2 Evaluation Board Schematic

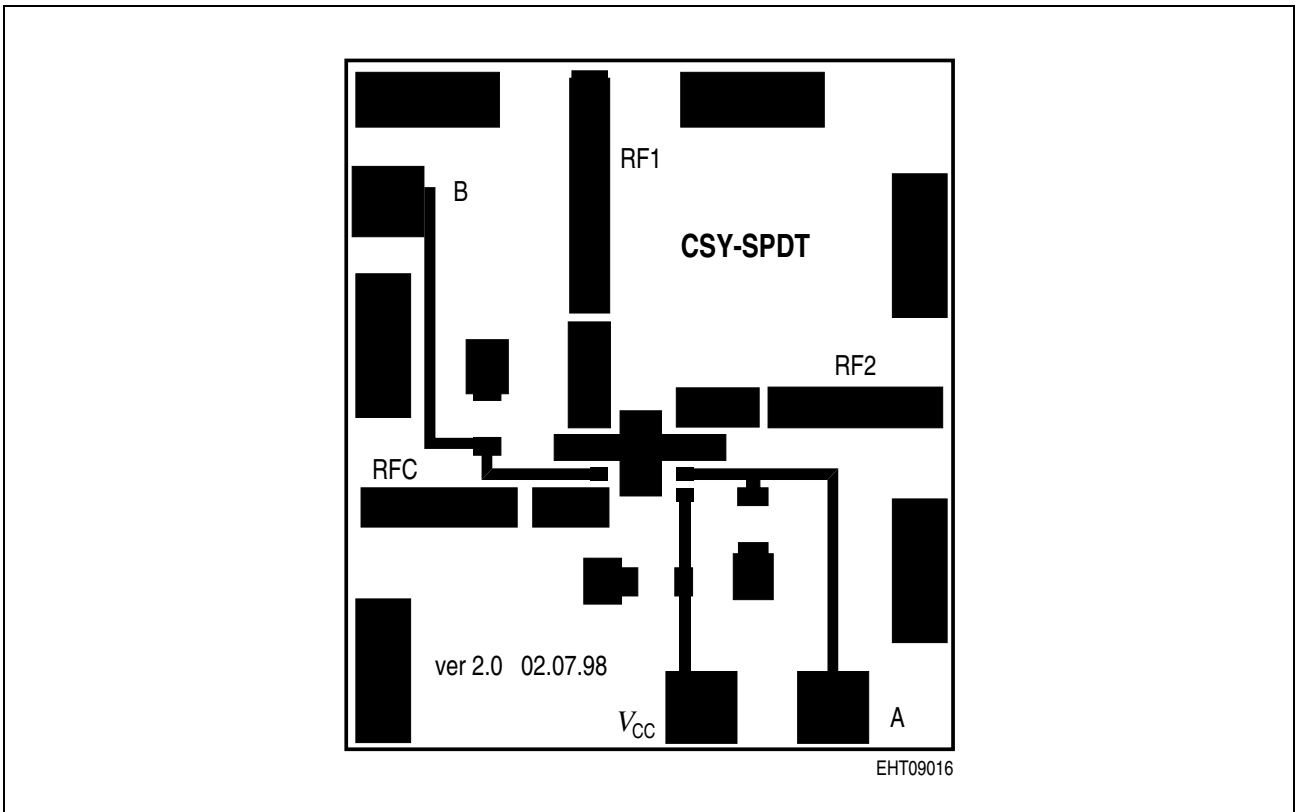
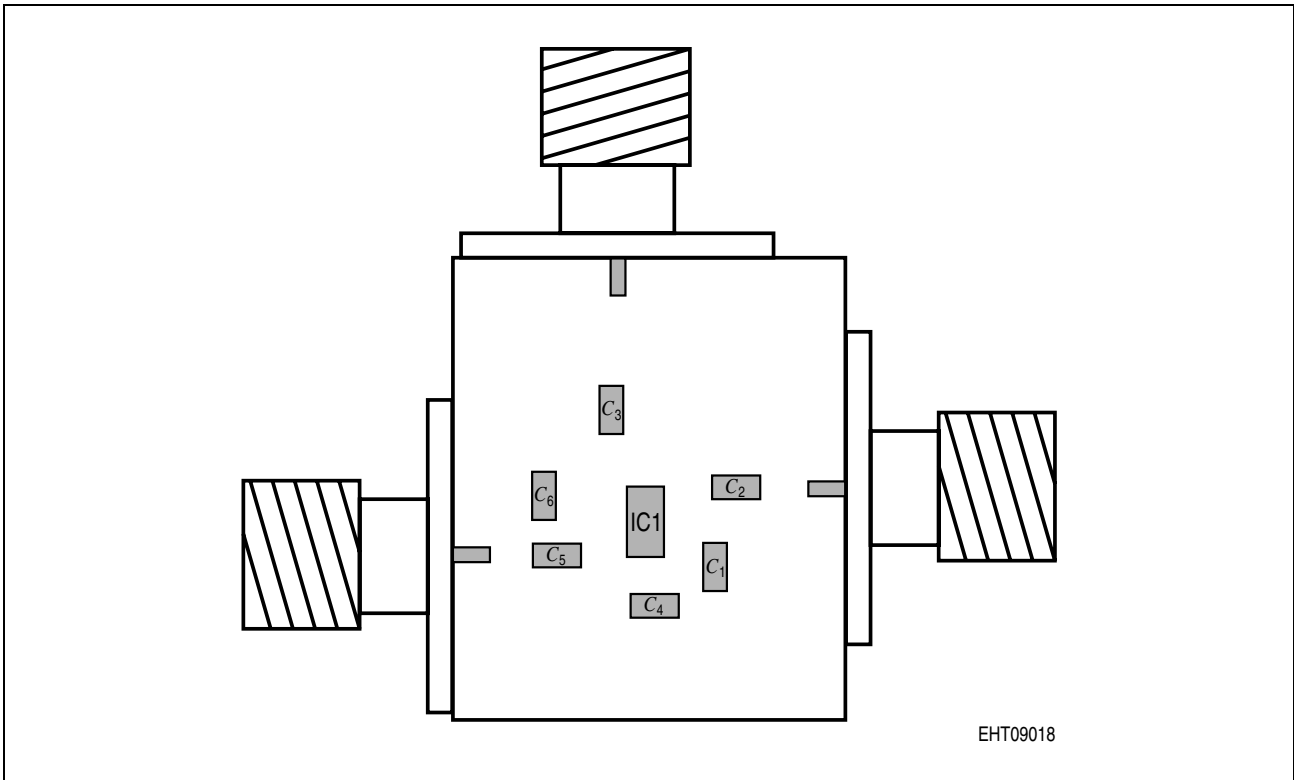


Figure 3 Evaluation Board (3:1 Scale)



**Figure 4** Board Material: TLX-9-0150 (TACONIC);  $\epsilon_r = 2.4$ ;  $h = 0.4$  mm

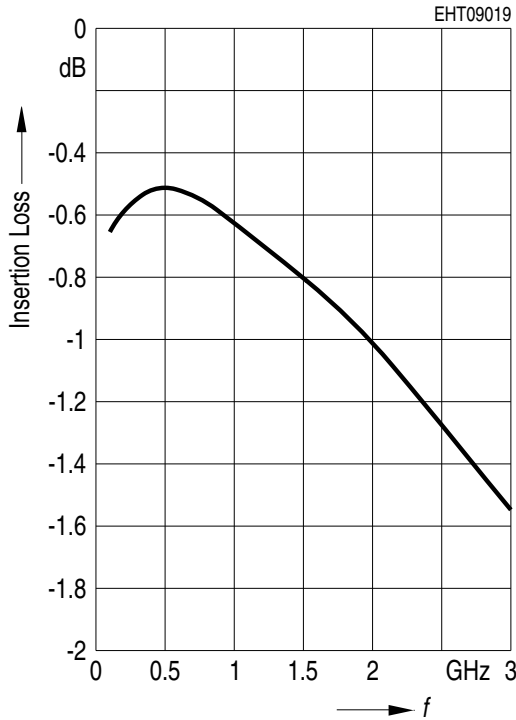
**Evaluation Board Parts List**

Part Type	Position	Description	Manufacturer	Part Number
Capacitor	$C_2, C_3, C_5$	100 pF 0603	Epcos	–
Capacitor	$C_1, C_4, C_6$	1 nF 0603	Epcos	–

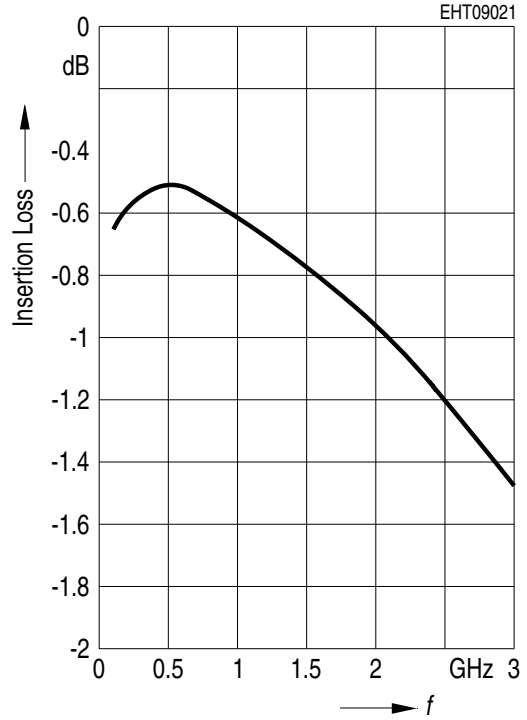
**Measured Results**

(all Ports connected to 50  $\Omega$ ;  $P_{IN} = 10$  dBm unless otherwise specified)

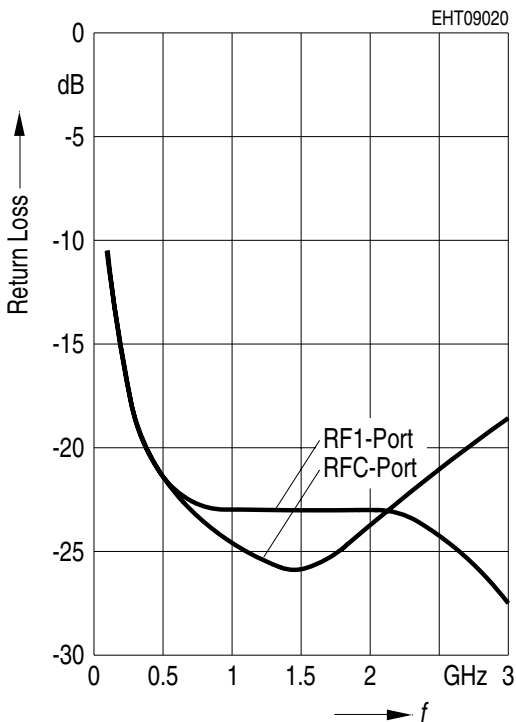
**Insertion Loss (RFC, RF1 - Port @  
A = 0 V; B = 3 V;  $V_{CC} = 3$  V)**



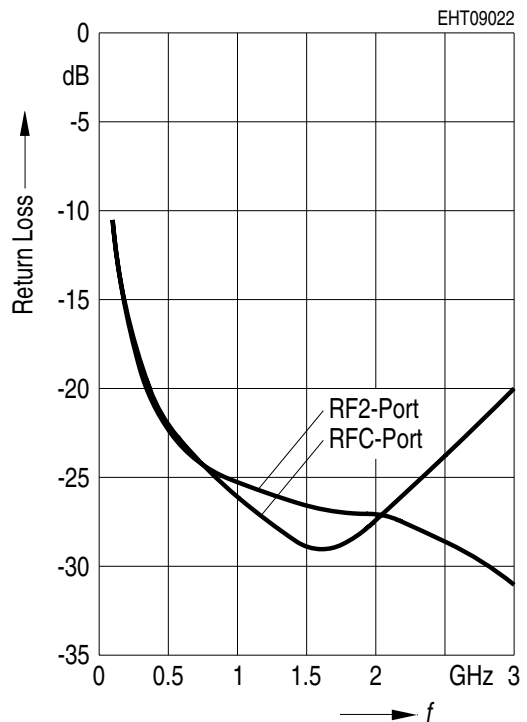
**Insertion Loss (RFC, RF2 - Port @  
A = 3 V; B = 0 V;  $V_{CC} = 3$  V)**



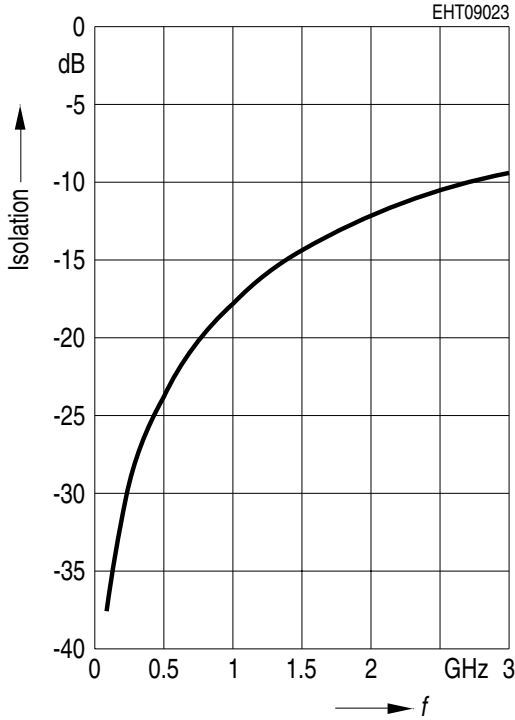
**Return Loss (RFC, RF1 - Port @  
A = 0 V; B = 3 V;  $V_{CC} = 3$  V)**



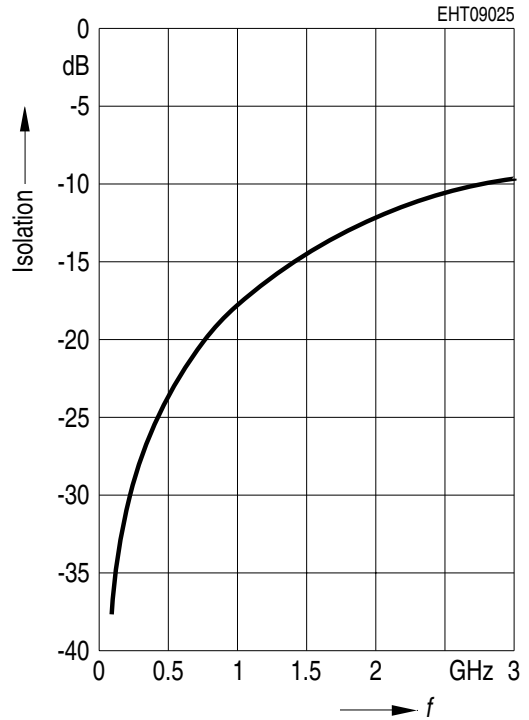
**Return Loss (RFC, RF2 - Port @  
A = 3 V; B = 0 V;  $V_{CC} = 3$  V)**



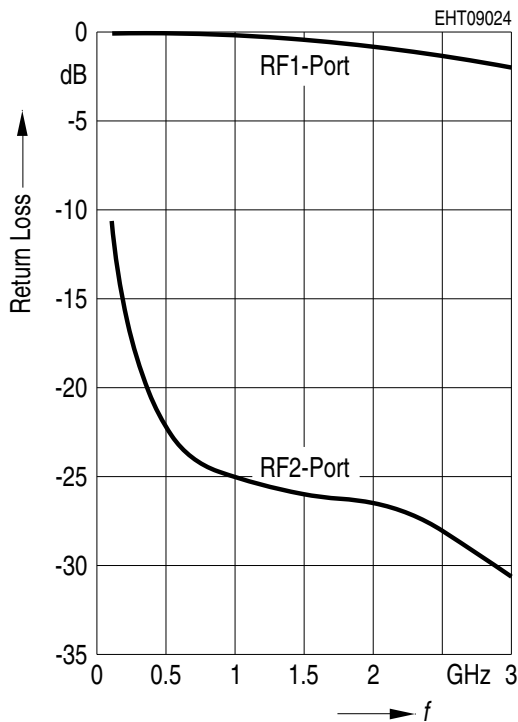
**Isolation (RF1, RF2 - Port @**  
 $A = 3\text{ V}; B = 0\text{ V}; V_{CC} = 3\text{ V}$ )



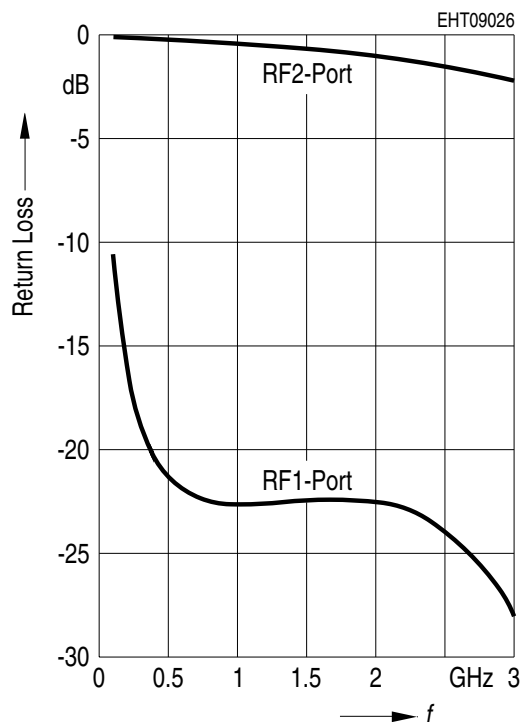
**Isolation (RF1, RF2 - Port @**  
 $A = 0\text{ V}; B = 3\text{ V}; V_{CC} = 3\text{ V}$ )



**Return Loss (RF1, RF2 - Port @**  
 $A = 3\text{ V}; B = 0\text{ V}; V_{CC} = 3\text{ V}$ )

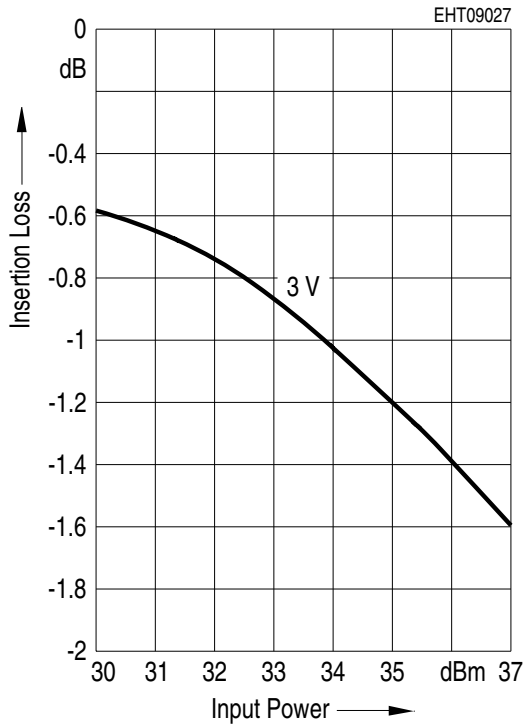


**Return Loss (RF1, RF2 - Port @**  
 $A = 0\text{ V}; B = 3\text{ V}; V_{CC} = 3\text{ V}$ )



**Insertion Loss vs. Input Power**

(RF2 - RFC @  $A = V_{CC} = 3\text{ V}$ ;  $B = 0\text{ V}$ ;  
 $f = 900\text{ MHz}$  pulsed:  $T_{ON} = 577\text{ }\mu\text{S}$ ;  
 12.5% duty cycle GSM-Signal)



**Isolation vs. Input Power**

(RF2 - RF1 @  $A = V_{CC} = 3\text{ V}$ ;  $B = 0\text{ V}$ ;  
 $f = 900\text{ MHz}$  pulsed:  $T_{ON} = 577\text{ }\mu\text{S}$ ;  
 12.5% duty cycle GSM-Signal)

